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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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## Silicon Planar Zener Diode for Surge Absorb

## RENESAS

ADE-208-822A (Z)

Rev.1 Nov. 2001

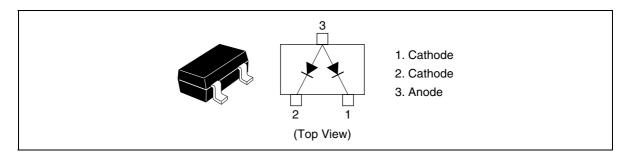
#### Features

- HZM6.8ZMWA has two devices in a monolithic, and can absorb surge.
- Low capacitance (C = 25 pF max) and can protect ESD of signal line.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

#### **Ordering Information**

Туре No.	Laser Mark	Package Code
HZM6.8ZMWA	68N	MPAK

#### **Pin Arrangement**



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit	
Power dissipation	Pd *	200	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Note: Two device total, See Fig.2.

#### **Electrical Characteristics**\*<sup>1</sup>

 $(Ta = 25^{\circ}C)$ 

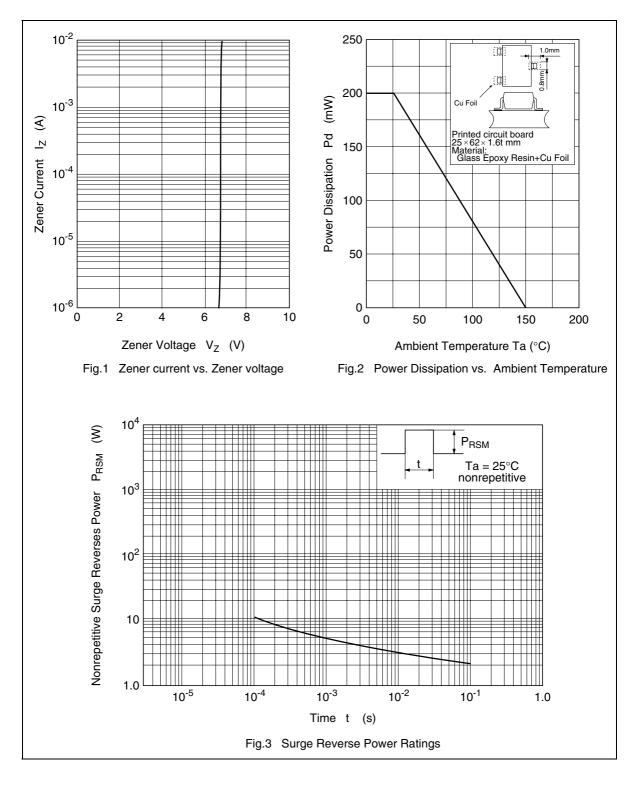
Item	Symbol	Min	Тур	Мах	Unit	Test Condition
Zener voltage	Vz	6.47	_	7.00	V	$I_z = 5 \text{ mA}, 40 \text{ ms pulse}$
Reverse current	I <sub>R</sub>	_	_	2	μA	V <sub>R</sub> = 3.5 V
Capacitance	С	_	_	25	pF	$V_{_{\mathrm{R}}} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$
Dynamic resistance	r <sub>d</sub>	_	_	30	Ω	$I_z = 5 \text{ mA}$
ESD-Capability * <sup>2.</sup> * <sup>3</sup>	_	20	—	—	kV	C = 150 pF, R = 330 $\Omega$ , Both forward and reverse direction 10 pulse

Notes: 1. Per one device.

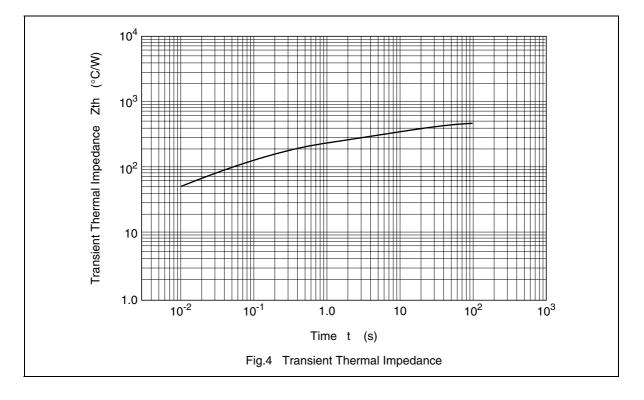
2. Failure criterion ;  $I_{_{\rm R}}\!>\!2~\mu A$  at  $V_{_{\rm R}}\!=3.5~V.$ 

3. Between cathode and anode.

#### **Main Characteristic**

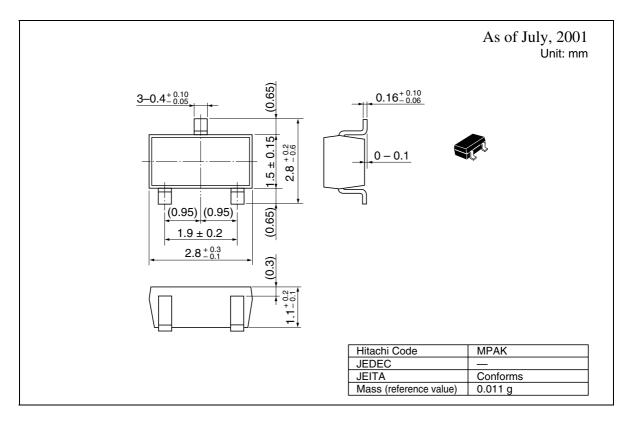


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### **Package Dimensions**



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